Abstracts

Improved FET Noise Model Extraction Method for Statistical Model Development

S. Pritchett, A. Fernandez, D. Bridges and K. Whelan. "Improved FET Noise Model Extraction Method for Statistical Model Development." 1995 MTT-S International Microwave Symposium Digest 95.2 (1995 Vol. II [MWSYM]): 943-946.

An analytic method is presented for extracting gate-source leakage resistance, R/sub gs/, from S-parameter measurements >=500 MHz. Subsequent noise source parameter extraction is frequency independent. Consequently, model parameter optimization is eliminated and physical correlations between parameters preserved. Compact statistical noise models can then be developed using the Principal Component method. R/sub gs/ also improves modeled low-frequency stability characteristics.

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